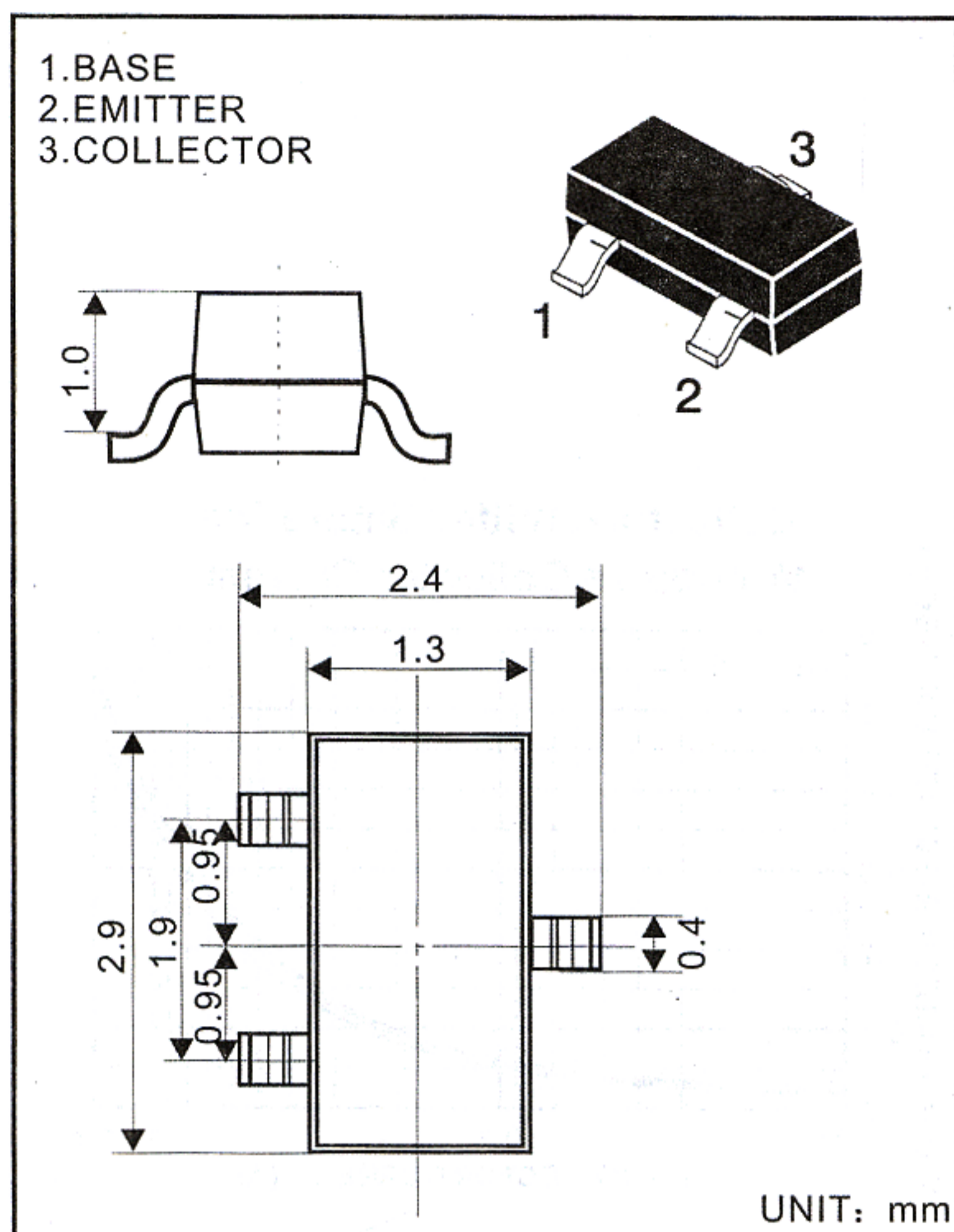


BC807-16/25/40LT1 TRANSISTOR (PNP)



FEATURES

Power dissipation

P_{CM} : 0.3 W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : -0.5 A

Collector-base voltage

$V_{(BR)CBO}$: -50V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

ELECTRICAL CHARACTERISTICS

($T_{amp}=25^{\circ}C$ unless otherwise specified)

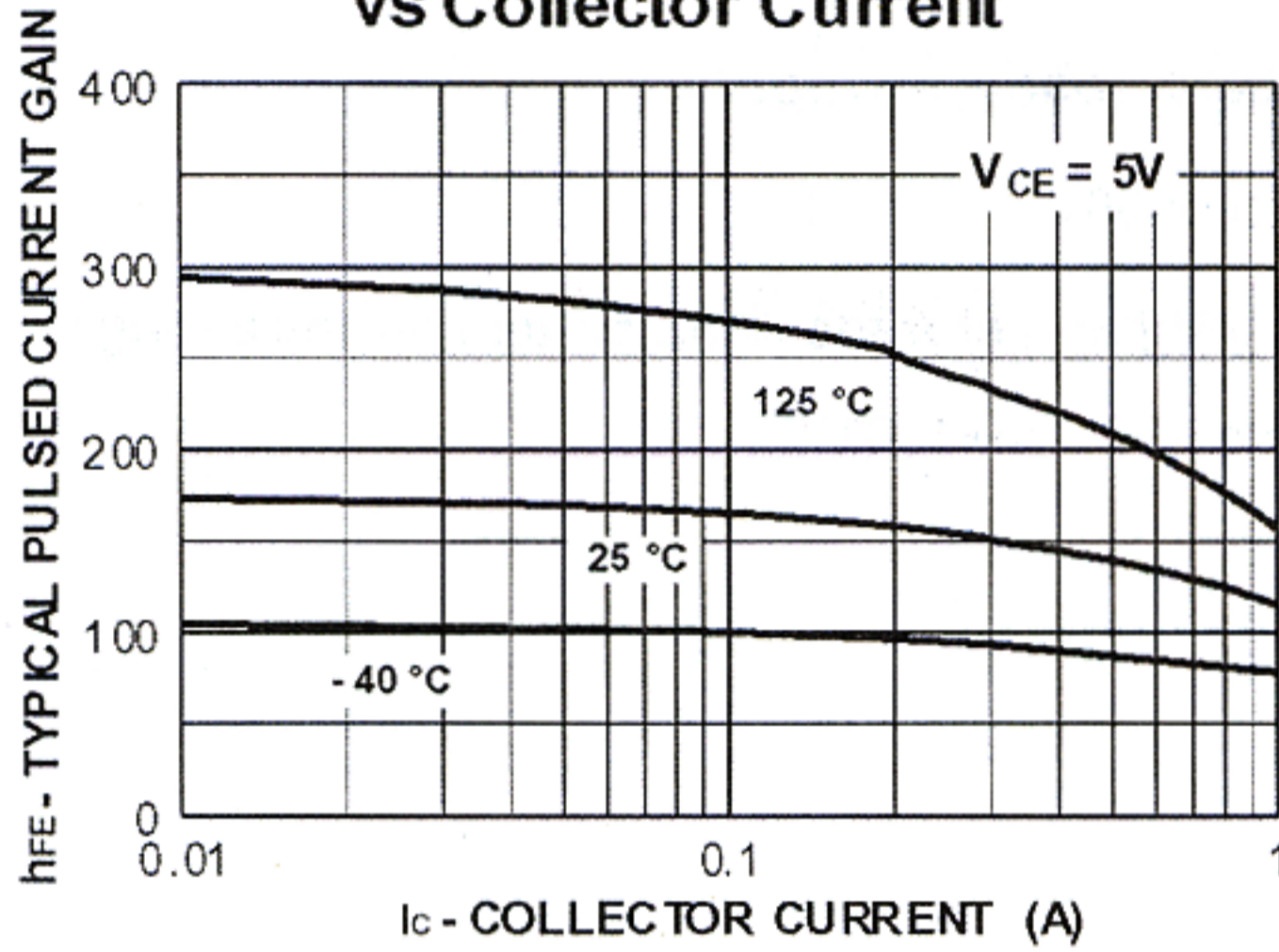
Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -10mA, I_E = 0$	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10mA, I_B = 0$	-45			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -1\mu A, I_B = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -45V, I_E = 0$			-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -40V, I_B = 0$			-0.2	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4V, I_C = 0$			-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -1V, I_C = -100mA$	100 160 250		250 400 600	
	$h_{FE(2)}$	$V_{CE} = -1V, I_C = -500mA$	40			
Collector-emitter saturation voltage	V_{CEsat}	$I_C = -500mA, I_B = -50mA$			-0.7	V
Base-emitter saturation voltage	V_{BEsat}	$I_C = -500mA, I_B = -50mA$			-1.2	V
Transition frequency	f_T	$V_{CE} = -5V, I_C = -10mA, f = 100MHz$	100			MHz

DEVICE MARKING : BC807-16LT1=5A1;BC807-25=5B;BC807-40LT1=5C

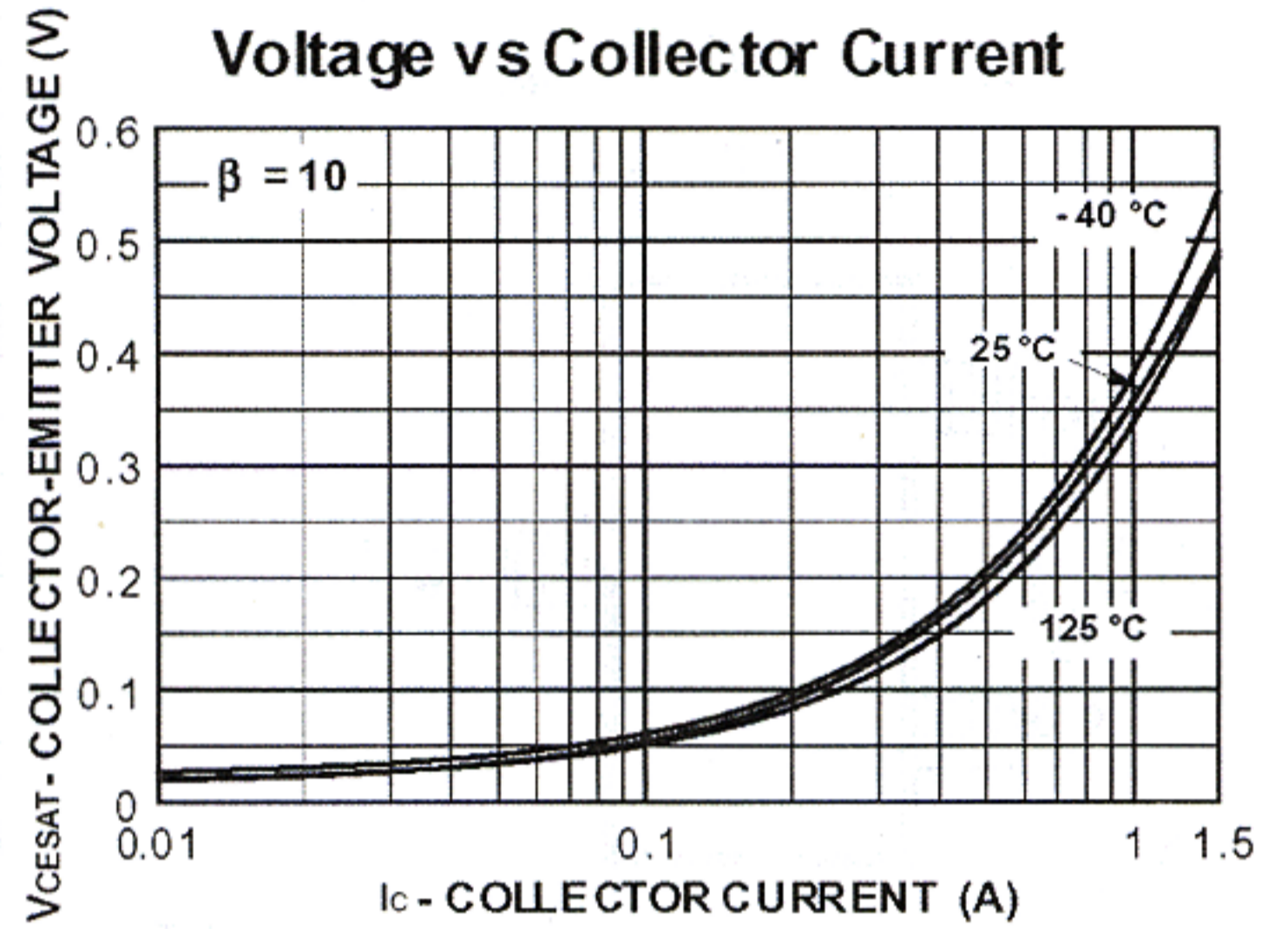
Typical Characteristics

BC807-16,25,40LT1

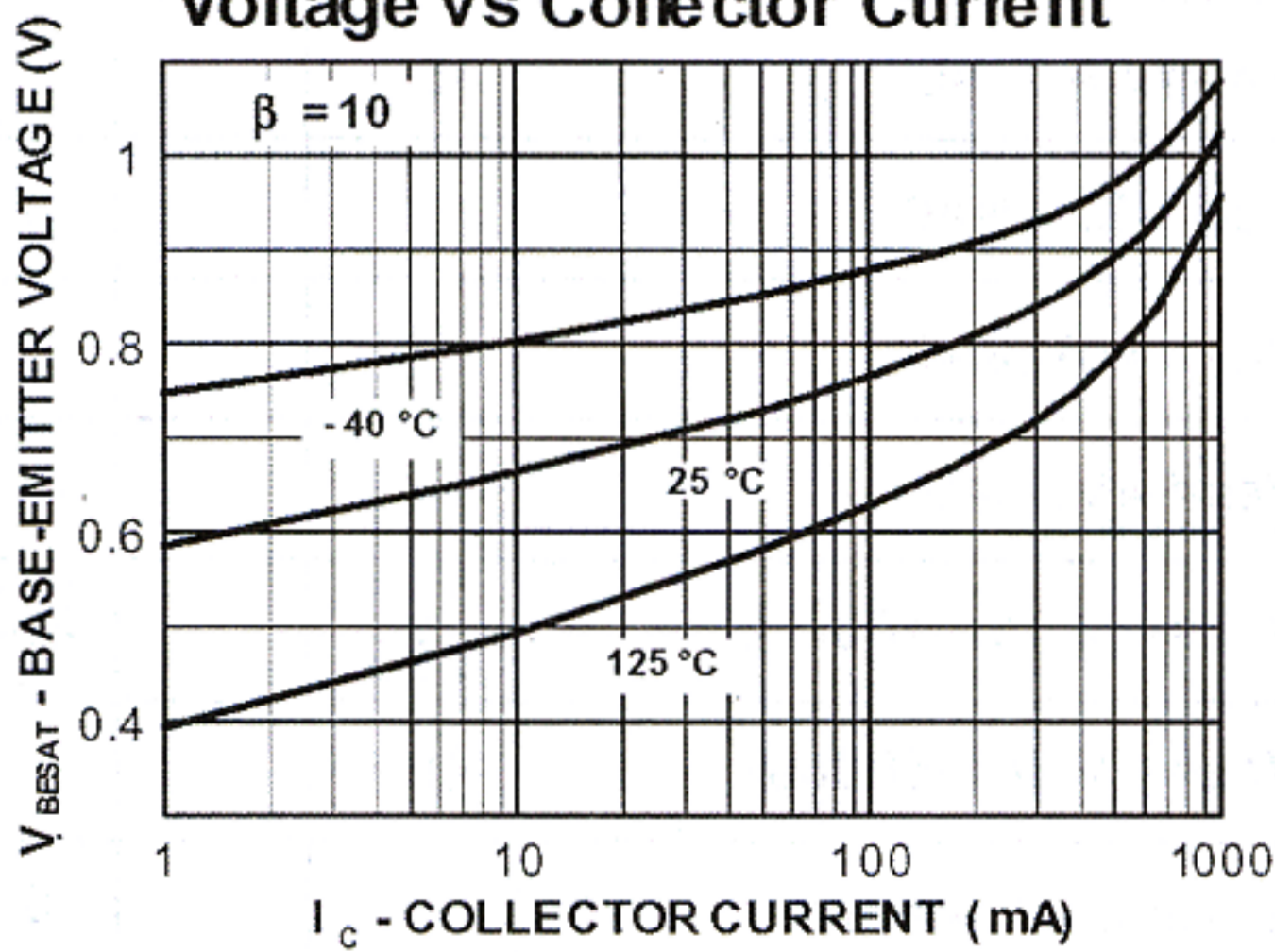
Typical Pulsed Current Gain vs Collector Current



Collector-Emitter Saturation Voltage vs Collector Current



Base-Emitter Saturation Voltage vs Collector Current



Gain Bandwidth Product vs Collector Current

